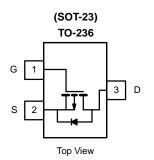
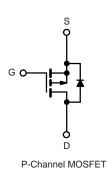


P-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}$ (Ω) Typ.	I _D (A) ^a	Q _g (Typ.)		
	0.046 at V _{GS} = - 10 V	- 5.6			
- 30	0.049 at V _{GS} = - 6 V	- 5	11.4 nC		
	0.054 at V _{GS} = - 4.5 V	-4.5			





APPLICATIONS

• 100 % R_g Tested

FEATURES

- For Mobile Computing
 - Load Switch
 - Notebook Adaptor Switch

• TrenchFET® Power MOSFET

- DC/DC Converter



Parameter	Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	- 30	V
Gate-Source Voltage		V _{GS}	± 20	V
	T _C = 25 °C		- 5.6	
Continuous Proin Current (T. 150 °C)	T _C = 70 °C	,	- 5.1	
Continuous Drain Current (T _J = 150 °C)	T _A = 25 °C	l _D	- 5.4 ^{b,c}	
	T _A = 70 °C		- 4.3 ^{b,c}	А
Pulsed Drain Current (t = 100 μs)		I _{DM}	- 18	
Ocation of October Bridge October	T _C = 25 °C		- 2.1	
Continous Source-Drain Diode Current	T _A = 25 °C	I _S	- 1 ^{b,c}	
	T _C = 25 °C		2.5	
Maniana Danian Diaginatian	T _C = 70 °C		1.6	W
Maximum Power Dissipation	T _A = 25 °C	P _D	1.25 ^{b,c}	VV
	T _A = 70 °C		0.8 ^{b,c}	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Typical	Maximum	Unit			
Maximum Junction-to-Ambient ^{b,d}	t ≤ 5 s	R _{thJA}	75	100	°C/W		
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	40	50	C/VV		

Notes:

- a. Based on T_C = 25 °C. b. Surface mounted on 1" x 1" FR4 board.
- c. t = 5 s.
- d. Maximum under steady state conditions is 166 °C/W.



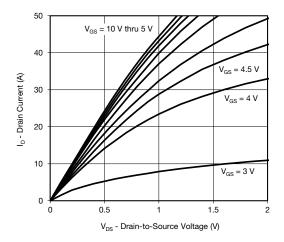
SPECIFICATIONS ($T_J = 25 ^{\circ}\text{C}$, Parameter	Symbol	Test Conditions	Min.	Tvn	Max.	Unit	
Static	Symbol	rest Conditions	WIII.	Тур.	wax.	Unit	
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = - 250 μA	- 30			V	
	ΔV _{DS} /T _J	VGS = 0 V, 1D = 200 μA	- 30	10		V	
V _{DS} Temperature Coefficient		I _D = - 250 μA	- 19		mV/°C		
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$)/		4	0.0		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	- 0.5		- 2.0	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -30 V, V _{GS} = 0 V V _{DS} = -30 V, V _{GS} = 0 V, T _J = 55 °C			- 1 - 5	μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le 0.000$ $V_{GS} = -10 \text{ V}$	- 2.5			Α	
On State Brain Surrent	·D(on)	$V_{GS} = -10 \text{ V}, I_{D} = -4.4 \text{ A}$	2.0	0.046			
Drain-Source On-State Resistance ^a	P	V _{GS} = -6 V, I _D = -4 A	-				
Dialit-Source Off-State Resistance	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 3.6 A		0.049		Ω	
Family of Transport distance	~	V _{GS} = -4.5 V, I _D = -3.4 A		0.054			
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 3.4 A		18	<u> </u>	S	
Dynamic ^b				1	1	1	
Input Capacitance	C _{iss}			1295		pF	
Output Capacitance	C _{oss}	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		150			
Reverse Transfer Capacitance	C_{rss}			130			
Total Gate Charge	Q _g	$V_{DS} = -15 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -5.4 \text{ A}$		24 36			
-				11.4	17	nC	
Gate-Source Charge	Q _{gs}	$V_{DS} = -15 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -5.4 \text{ A}$		3.4			
Gate-Drain Charge	Q_{gd}			3.8			
Gate Resistance	R_g	f = 1 MHz	1.5	7.7	15.4	Ω	
Turn-On Delay Time	$t_{d(on)}$			13	20		
Rise Time	t _r	V_{DD} = - 15 V, R_L = 3.5 Ω		4	8		
Turn-Off Delay Time		$I_D \cong -4.3 \text{ A}, V_{GEN} = -10 \text{ V}, R_g = 1 \Omega$		38	57		
Fall Time	t _f			6	12		
Turn-On Delay Time	t _{d(on)}			28	42	ns	
Rise Time	t _r	$V_{DD} = -15 \text{ V}, R_{L} = 3.5 \Omega$		16	24		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong -4.3 \text{ A}, V_{GEN} = -4.5 \text{ V}, R_g = 1 \Omega$		30	45	1	
Fall Time	t _f			10	20		
Drain-Source Body Diode Characteristic	s			l			
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			- 2.1		
Pulse Diode Forward Current (t = 100 μs)	I _{SM}				- 80	A	
Body Diode Voltage	V _{SD}	I _S = -4.3 A, V _{GS} = 0 V		- 0.8	- 1.2	V	
Body Diode Reverse Recovery Time	t _{rr}	- 55		15	23	ns	
Body Diode Reverse Recovery Charge Q _{rr}		1		7	14	nC	
Reverse Recovery Fall Time		$I_F = -4.3 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, I_J = 25 \text{ °C}$		8	 	ns	
Reverse Recovery Rise Time	t _b			7	-		

Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

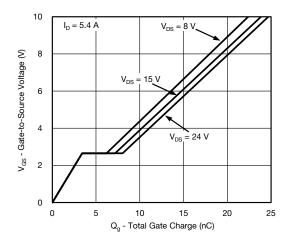




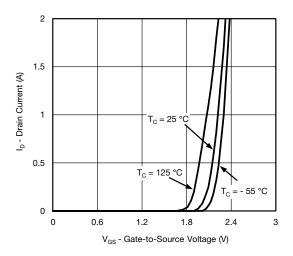
Output Characteristics



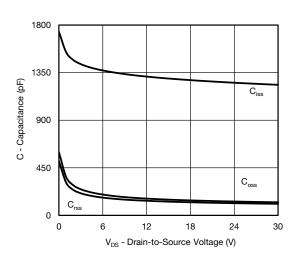
On-Resistance vs. Drain Current



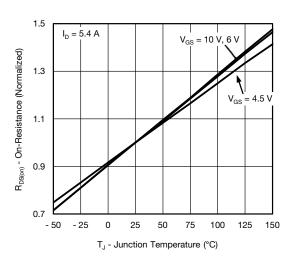
Gate Charge



Transfer Characteristics

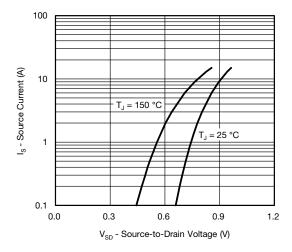


Capacitance

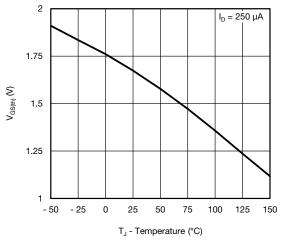


On-Resistance vs. Junction Temperature

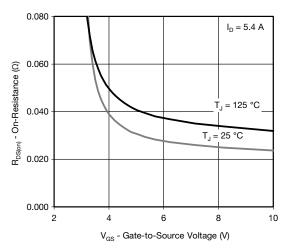




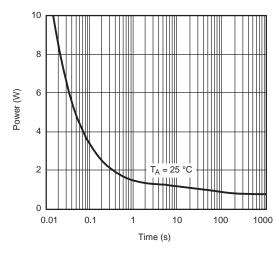
Source-Drain Diode Forward Voltage



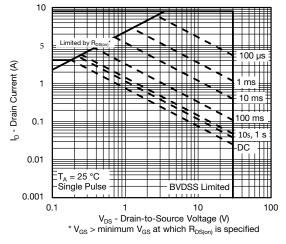
Threshold Voltage



On-Resistance vs. Gate-to-Source Voltage

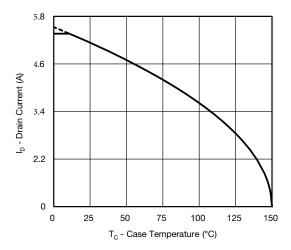


Single Pulse Power (Junction-to-Ambient)

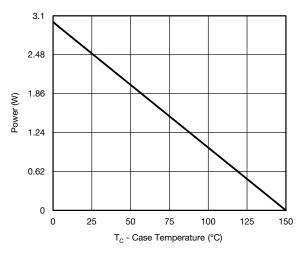


Safe Operating Area, Junction-to-Ambient

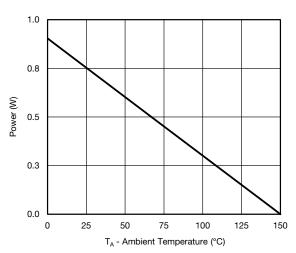




Current Derating*



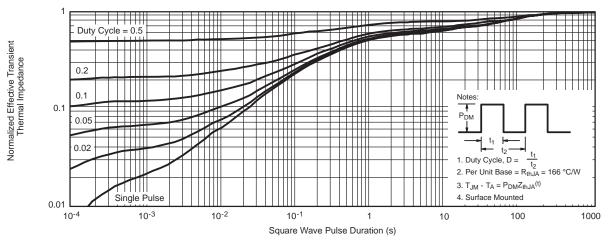




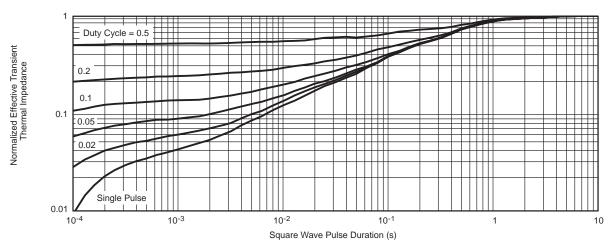
Power, Junction-to-Ambient

^{*} The power dissipation P_D is based on $T_{J(max.)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.





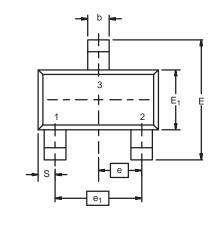
Normalized Thermal Transient Impedance, Junction-to-Ambient

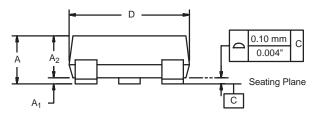


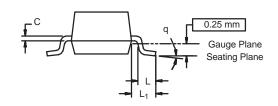
Normalized Thermal Transient Impedance, Junction-to-Foot



SOT-23 (TO-236): 3-LEAD





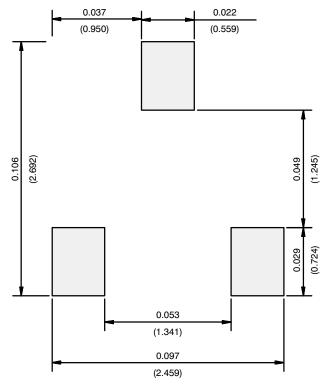


Dim -	MILLIM	IETERS	INCHES		
	Min	Max	Min	Max	
Α	0.89	1.12	0.035	0.044	
A ₁	0.01	0.10	0.0004	0.004	
A ₂	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E ₁	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e ₁	1.90 BSC		0.0748 Ref		
L	0.40	0.60	0.016	0.024	
L ₁	0.64 Ref		0.025 Ref		
S	0.50 Ref		0.020 Ref		
q	3°	8°	3°	8°	
ECN: S-03946-Rev. K. 09-	Jul-01	•			

DWG: 5479



RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads Dimensions in Inches/(mm)



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